

Amendments to the Claims

1-19 (canceled)

20. (original) In an electron-beam (EB) microlithographic exposure method in which an electron beam is directed to a reticle assembly, defining a pattern, so as to acquire an ability to form an image of the pattern on a substrate, an improvement comprising:

on the reticle assembly defining a first pattern portion on at least one scattering-stencil reticle portion and defining a second pattern portion on at least one scattering-membrane reticle portion; and

using the electron beam, transferring the pattern portions from each reticle portion to the substrate so as to produce a stitched-together image of the pattern on the substrate.

21. (original) The method of claim 20, wherein:

each of the reticle portions is divided into respective subfields each defining a respective portion of the pattern; and

the step of transferring the pattern portions comprises exposing the subfields individually to respective locations on the substrate so as to stitch together images of the respective portions of the pattern on the substrate.

22. (original) The method of claim 20, wherein:

each scattering-stencil reticle portion comprises a respective reticle membrane defining pattern elements by respective through-holes in the reticle membrane; and

each scattering-membrane reticle portion comprises a respective reticle membrane including a pattern-defining layer made of a material different from a material used to form the respective reticle membrane.

23-33. (canceled)